

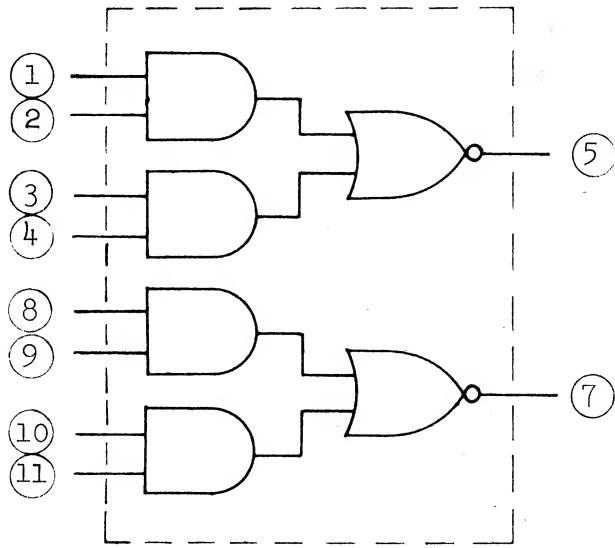


Preliminary Specifications

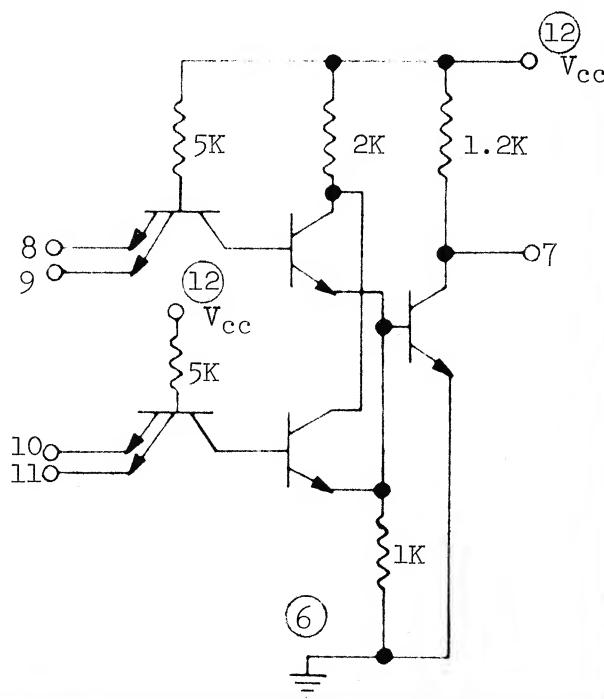
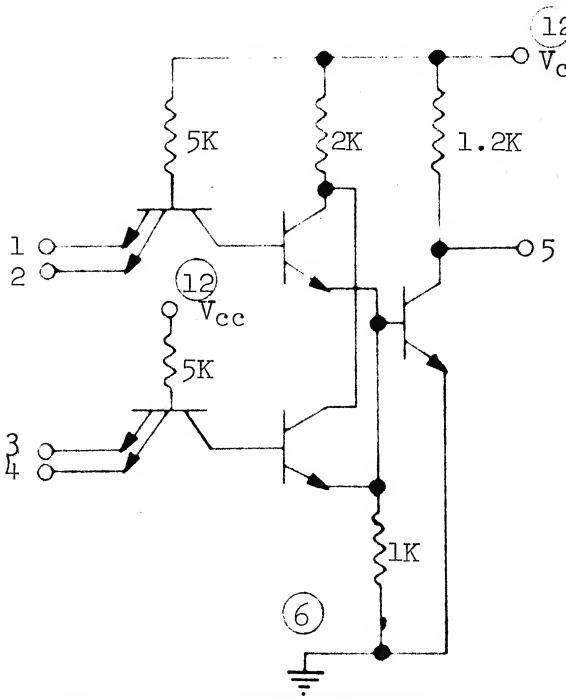
DESCRIPTION

The SN676 is a dual TTL Exclusive OR gate with low propagation delay and high noise immunity designed to operate over the full military temperature range of -55°C to $+125^{\circ}\text{C}$. The SN676 is fabricated using diffused planar epitaxial techniques.

August 1964

LOGIC DIAGRAMS

	Positive	Negative
5	$(1)(2) + (3)(4)$	$(1+2)(3+4)$
7	$(8)(9) + (10)(11)$	$(8+9)(10+11)$

NETWORK CIRCUIT DIAGRAMS

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POST OFFICE BOX 5012 • DALLAS 22, TEXAS

Preliminary Specifications

NETWORK CHARACTERISTICS

Absolute Maximum Ratings:

Supply Voltage	8 volts
Input Voltage	6 volts
Output Voltage	8 volts
Power Dissipation	200 mw
Operating Temperature	-55°C to +125°C

Network Electrical Characteristics

		Network Parameters									MIN	MAX	UNIT
Operating Supply Voltage											4.0	5.0	v
Fan-Out: Each Output Paralleled Output											7	5	
Off Voltage		PIN	1	2	3	4	8	9	10	11			
$V_{cc} = 4.0$ volts		5	0.8	4.5	0.8	4.5	-	-	-	-	2.3		v
Temperature +125°C		5	4.5	0.8	0.8	4.5	-	-	-	-	2.3		v
(See Figure 1)		5	0.8	4.5	4.5	0.8	-	-	-	-	2.3		v
		5	4.5	0.8	4.5	0.8	-	-	-	-	2.3		v
		7	-	-	-	-	0.8	4.5	0.8	4.5	2.3		v
		7	-	-	-	-	4.5	0.8	0.8	4.5	2.3		v
		7	-	-	-	-	0.8	4.5	4.5	0.8	2.3		v
		7	-	-	-	-	4.5	0.8	4.5	0.8	2.3		v
Saturation Voltage		PIN	1	2	3	4	8	9	10	11			
$V_{cc} = 4.0$ volts	+125°C	5	0	-	2.0	2.0	-	-	-	-	0.5		v
(See Figure 3)	+125°C	5	2.0	2.0	0	-	-	-	-	-	0.5		v
	+125°C	7	-	-	-	-	0	-	2.0	2.0	0.5		v
	+125°C	7	-	-	-	-	2.0	2.0	0	-	0.5		v
	+125°C	5	0	-	2.0	2.0	-	-	-	-	0.5		v
	+125°C	5	2.0	2.0	0	-	-	-	-	-	0.5		v
	+125°C	7	-	-	-	-	0	-	2.0	2.0	0.5		v
	+125°C	7	-	-	-	-	2.0	2.0	0	-	0.5		v
Input Short Current		PIN	1	2	3	4	8	9	10	11			
$V_{cc} = 4.5$ volts		1	0	4.5	-	-	-	-	-	-	1.2		ma
Temperature +125°C		3	-	-	0	4.5	-	-	-	-	1.2		ma
(See Figure 2)		8	-	-	-	-	0	4.5	-	-	1.2		ma
		10	-	-	-	-	-	-	-	0	4.5	1.2	ma
Noise Immunity										300			mv



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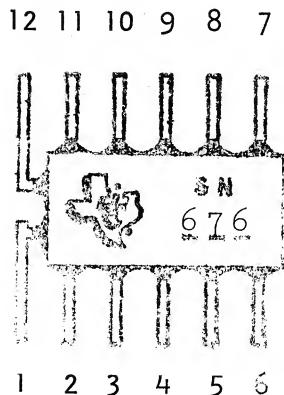
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NETWORK PARAMETERS											MIN	MAX	UNIT	
Output Short Current (See Figure 4)		PIN	1	2	3	4	8	9	10	11				
$+125^{\circ}\text{C}$ $V_{CC} = 4.5 \text{ v}$ -55°C		5	0	0	0	0	-	-	-	-		4.0	ma	
		7	-	-	-	-	0	0	0	0		4.0	ma	
		5	0	0	0	0	-	-	-	-	2.5		ma	
		7	-	-	-	-	0	0	0	0	2.5		ma	
Input Leakage Current (See Figure 5)		PIN	1	2	3	4	8	9	10	11				
$+125^{\circ}\text{C}$ $V_{CC} = 4.5 \text{ v}$		1	4.5	0	-	-	-	-	-	-		100	μa	
		2	0	4.5	-	-	-	-	-	-		100	μa	
		3	-	-	4.5	0	-	-	-	-		100	μa	
		4	-	-	0	4.5	-	-	-	-		100	μa	
		8	-	-	-	-	4.5	0	-	-		100	μa	
		9	-	-	-	-	0	4.5	-	-		100	μa	
		10	-	-	-	-	-	-	4.5	0		100	μa	
		11	-	-	-	-	-	-	0	4.5		100	μa	
On Current (from V_{CC})														
$V_{CC} = 5.0 \text{ v}$ $+125^{\circ}\text{C}$			5.0 volts on all inputs; outputs open								20		ma	
Off Current (from V_{CC})											8		ma	
$V_{CC} = 5.0 \text{ v}$ $+125^{\circ}\text{C}$			0 volts on all inputs; outputs open											
Leading Edge Delay ($\frac{T_+}{2}$)		PIN	1	2	3	4	8	9	10	11				
$V_{CC} = 4.0 \text{ v}$ -55°C $+125^{\circ}\text{C}$ -55°C		$+125^{\circ}\text{C}$	Δ	4.0	0	-	$\frac{pin}{2}$	4.0	0	-		35	ns	
			Δ	4.0	0	-	$\frac{pin}{5}$	4.0	0	-		35	ns	
		-55°C	0	-	Δ	4.0	0	-	$\frac{pin}{5}$	4.0		35	ns	
			0	-	Δ	4.0	0	-	$\frac{pin}{5}$	4.0		35	ns	
Trailing Edge Delay ($\frac{T_-}{2}$)		PIN	1	2	3	4	8	9	10	11				
$V_{CC} = 4.0 \text{ v}$ -55°C $+125^{\circ}\text{C}$ -55°C		$+125^{\circ}\text{C}$	Δ	4.0	0	-	$\frac{pin}{2}$	4.0	0	-		35	ns	
			Δ	4.0	0	-	$\frac{pin}{2}$	4.0	0	-		35	ns	
		-55°C	0	-	Δ	4.0	0	-	$\frac{pin}{5}$	4.0		35	ns	
			0	-	Δ	4.0	0	-	$\frac{pin}{5}$	4.0		35	ns	

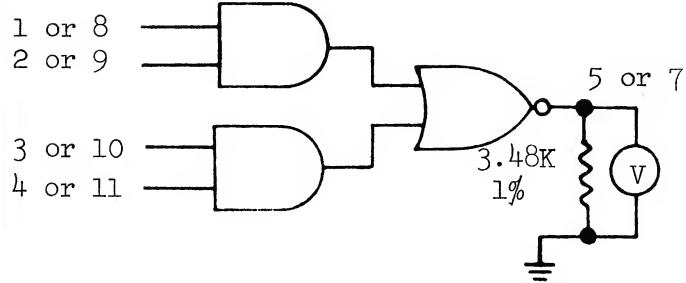


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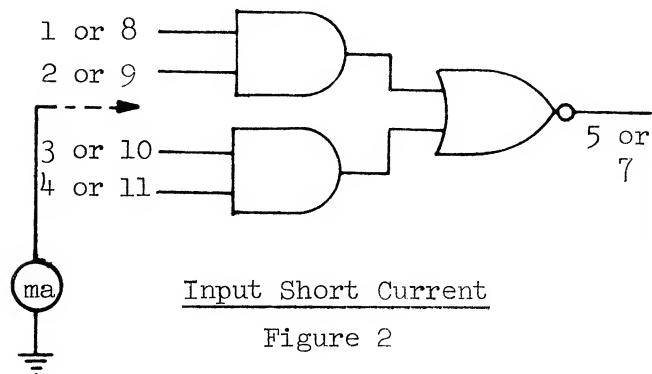
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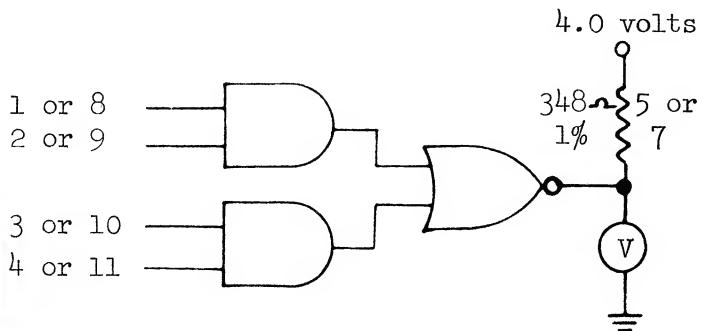
Package



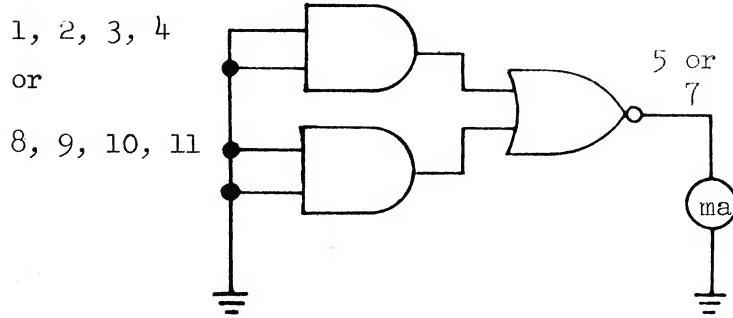
Off Voltage
Figure 1



Input Short Current

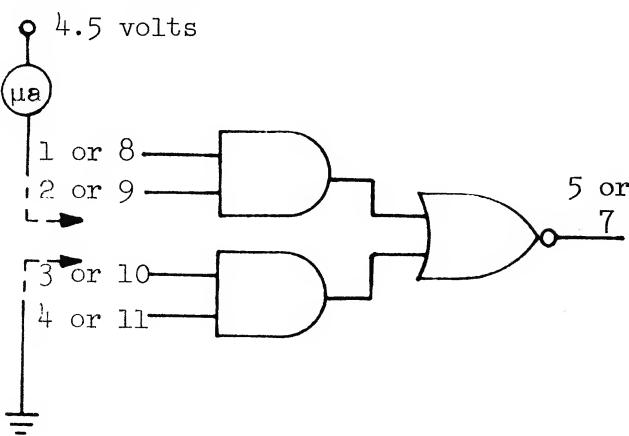


Saturation Voltage
Figure 3



Output Short Current

Figure 4



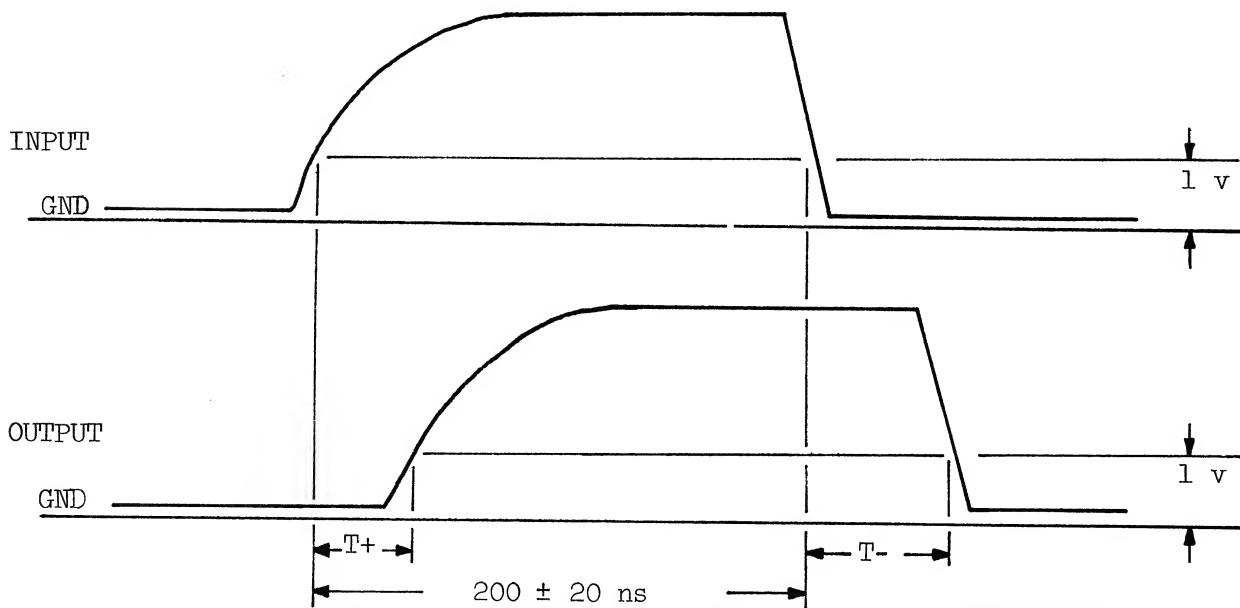
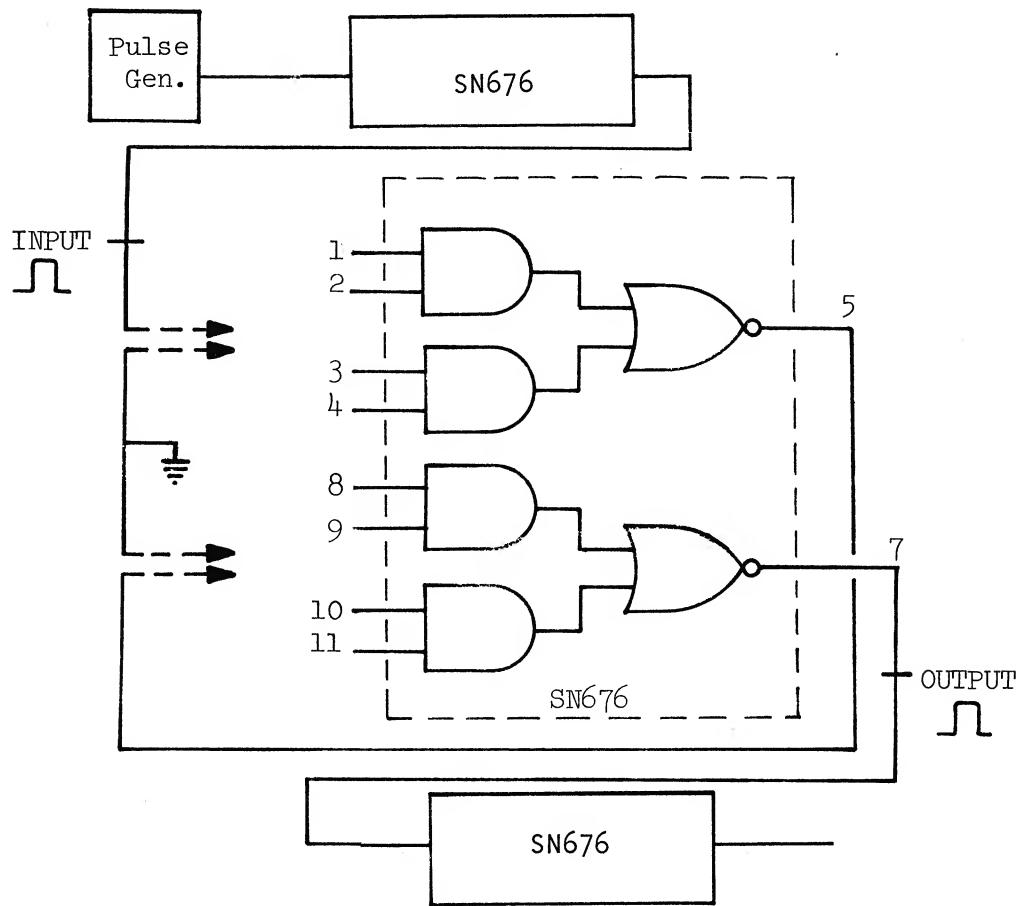
Input Leakage Current

Figure 5

Preliminary Specifications

PROPAGATION DELAY

Figure 6



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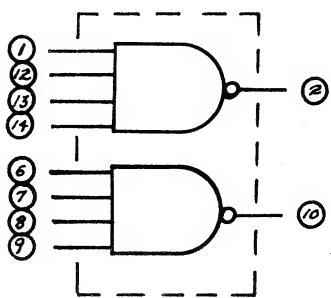
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Description

The SN742 is a dual, 4-input, TTL, positive NAND gate capable of driving large fan-out and high capacity loads over the full military temperature range of -55°C to $+125^{\circ}\text{C}$. The SN742 is fabricated using diffused planar double epitaxial techniques.

Logic DiagramLogic

Positive NAND:

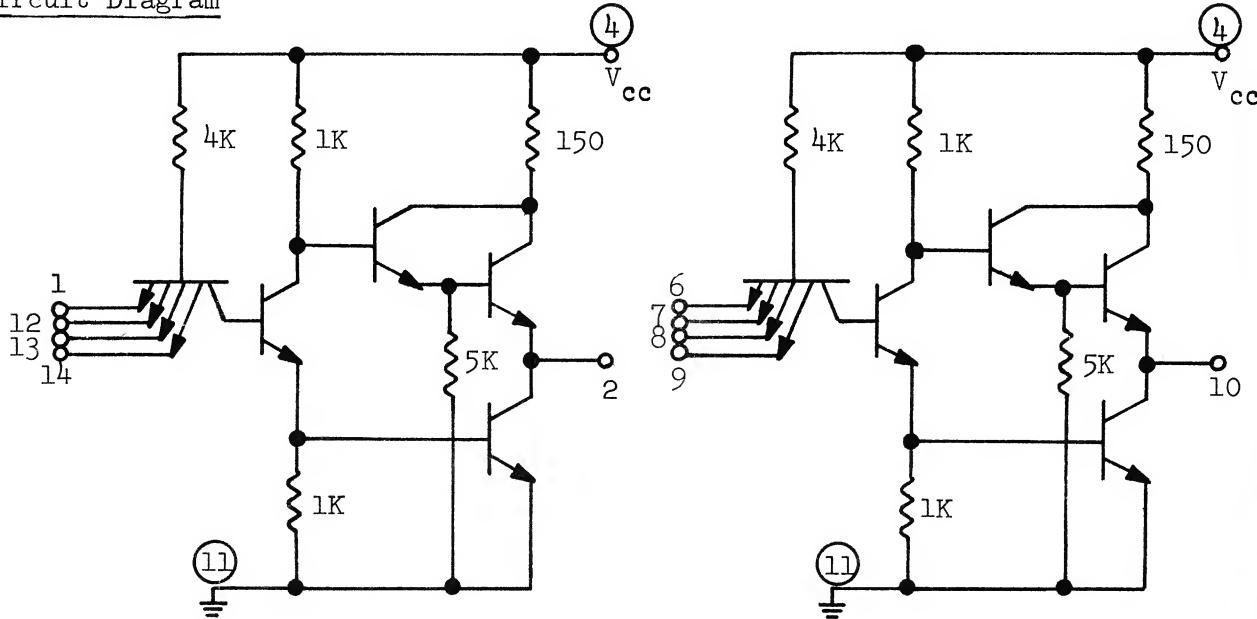
$$2 = \overline{(1)(12)(13)(14)}$$

$$10 = \overline{(6)(7)(8)(9)}$$

Negative NOR:

$$2 = \overline{1+12+13+14}$$

$$10 = \overline{6+7+8+9}$$

Circuit DiagramTypical Electrical Characteristics

Fan-out	15
Propagation Delay	25 ns
Noise Margin	600 mv
Power Dissipation	15 mw

August 1964



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PRELIMINARY SPECIFICATIONS

NETWORK CHARACTERISTICS

Absolute Maximum Ratings:

Supply Voltage	8 volts
Input Voltage	6 volts
Operating Ambient Temperature Range	-55°C to +125°C
Storage Temperature	-65°C to +150°C

All data applies for the following conditions unless otherwise noted:

Temperature: -55°C to +125°C

Fan-Out: 1 to 15

V_{cc} = 4.5 volts

NETWORK PARAMETERS									MIN	MAX	UNIT	
Operating Supply Voltage									4.5	5.5	v	
Fan-Out									1	15		
Output ON Level												
+125°C	PIN	1	12	13	14	6	7	8	9			
	2	-	-	-	-	-	-	-	-	0.5	v	
I ₁₀ = I ₂ = 20ma	10	-	-	-	-	-	-	-	-			
	2	2.0	2.0	2.0	2.0	-	-	-	-	0.5	v	
(See Figure 1)	10	-	-	-	-	2.0	2.0	2.0	2.0	0.5	v	
	2	2.0	2.0	2.0	2.0	-	-	-	-	2.4	v	
Output OFF Level												
I ₁₀ = I ₂ = -2ma	PIN	1	12	13	14	6	7	8	9			
	2	0.8	-	-	-	-	-	-	-	2.4	v	
(See Figure 2)	2	-	0.8	-	-	-	-	-	-	2.4	v	
	2	-	-	0.8	-	-	-	-	-	2.4	v	
+125°C	10	-	-	-	-	0.8	-	-	-	2.4	v	
	10	-	-	-	-	-	0.8	-	-	2.4	v	
(10	-	-	-	-	-	-	0.8	-	2.4	v	
	10	-	-	-	-	-	-	-	0.8	2.4	v	
(2	0.8	-	-	-	-	-	-	-	2.4	v	
	10	-	-	-	-	0.8	-	-	-	2.4	v	
Noise Immunity (Output ON Level) (Output OFF Level)									300		mv	
									400		mv	
Input Current												
V _{cc} = 5.5 volts	PIN	1	12	13	14	6	7	8	9			
	12	4.5	0	4.5	4.5	-	-	-	-	-1.6	ma	
(See Figure 4)	13	4.5	4.5	0	4.5	-	-	-	-	-1.6	ma	
	7	-	-	-	-	4.5	0	4.5	4.5			
(8	-	-	-	-	4.5	4.5	0	4.5	-1.6	ma	
	2	2.0	2.0	2.0	2.0	-	-	-	-	2.4	v	



NETWORK PARAMETERS										MIN	MAX	UNIT	
Input Leakage Current		PIN	1	12	13	14	6	7	8	9			
$V_{cc} = 5.5$ volts (See Figure 3)		1	4.5	0	0	0	-	-	-	-	150	ua	
		12	0	4.5	0	0	-	-	-	-	150	ua	
		13	0	0	4.5	0	-	-	-	-	150	ua	
		14	0	0	0	4.5	-	-	-	-	150	ua	
		6	-	-	-	-	4.5	0	0	0	150	ua	
		7	-	-	-	-	0	4.5	0	0	150	ua	
		8	-	-	-	-	0	0	4.5	0	150	ua	
		9	-	-	-	-	0	0	0	4.5	150	ua	
		1	5.5	0	0	0	-	-	-	-	1.0	ma	
		12	0	5.5	0	0	-	-	-	-	1.0	ma	
		13	0	0	5.5	0	-	-	-	-	1.0	ma	
		14	0	0	0	5.5	-	-	-	-	1.0	ma	
		6	-	-	-	-	5.5	-	-	-	1.0	ma	
		7	-	-	-	-	0	5.5	0	0	1.0	ma	
		8	-	-	-	-	0	0	5.5	0	1.0	ma	
		9	-	-	-	-	0	0	0	5.5	1.0	ma	
Short Current (See Fig. 5)		PIN	1	12	13	14	6	7	8	9			
$V_{cc} = 5.5$ volts		2	0	-	-	-	-	-	-	-	-20	-45	ma
Pins 2 and 10 = 0 volts		10	-	-	-	-	0	-	-	-	-20	-45	ma
Power Drain (From V_{cc})		PIN	1	12	13	14	6	7	8	9			
$V_{cc} = 5.5$ volts		4	0	-	-	-	0	-	-	-		6	ma
		4	-	-	-	-	-	-	-	-		12	ma
Current (I_4) of Breakdown Voltage ($V_{cc} = 8$ volts) Pins 1 and 6 = 0 volts Temperature 25°C											12	ma	

SWITCHING TIME					MIN	MAX	UNIT
Delay Time (t_d) (See Figure 7)	Fan-Out = 15	$C = 100$ pf				50	ns
		$C = 500$ pf				80	ns
Rise Time (t_r) (See Figure 7)	Fan-Out = 1 and 15	$C = 100$ pf				45	ns
		$C = 500$ pf				70	ns
Fall Time (t_f) (See Figure 7)	Fan-Out = 15	$C = 100$ pf				35	ns
		$C = 500$ pf				50	ns
Storage Time (t_s) (See Figure 7)	Fan-Out	$C = 100$ pf				65	ns
		$C = 500$ pf				100	ns



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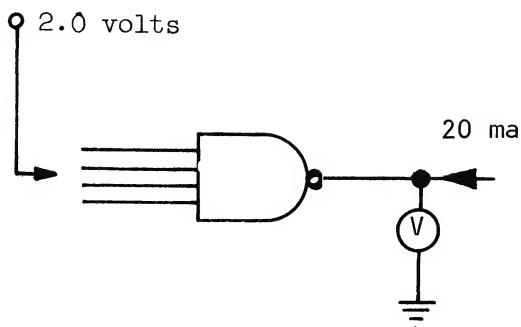
Output On Level

Fig. 1

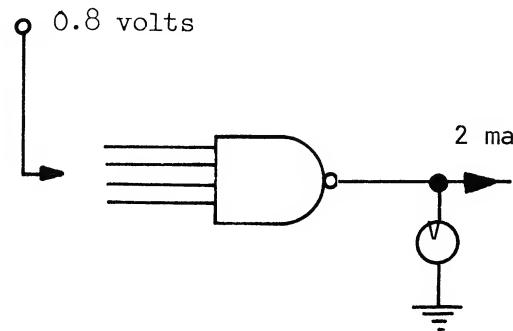
Output Off Level

Fig. 2

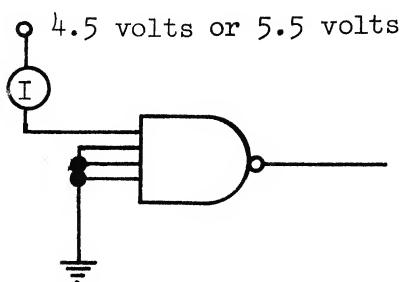
Input Leakage Current

Fig. 3

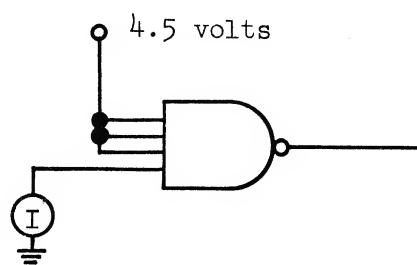
Input Current

Fig. 4

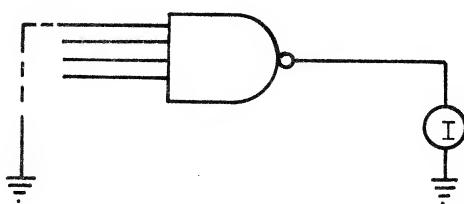
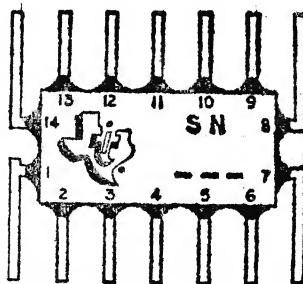
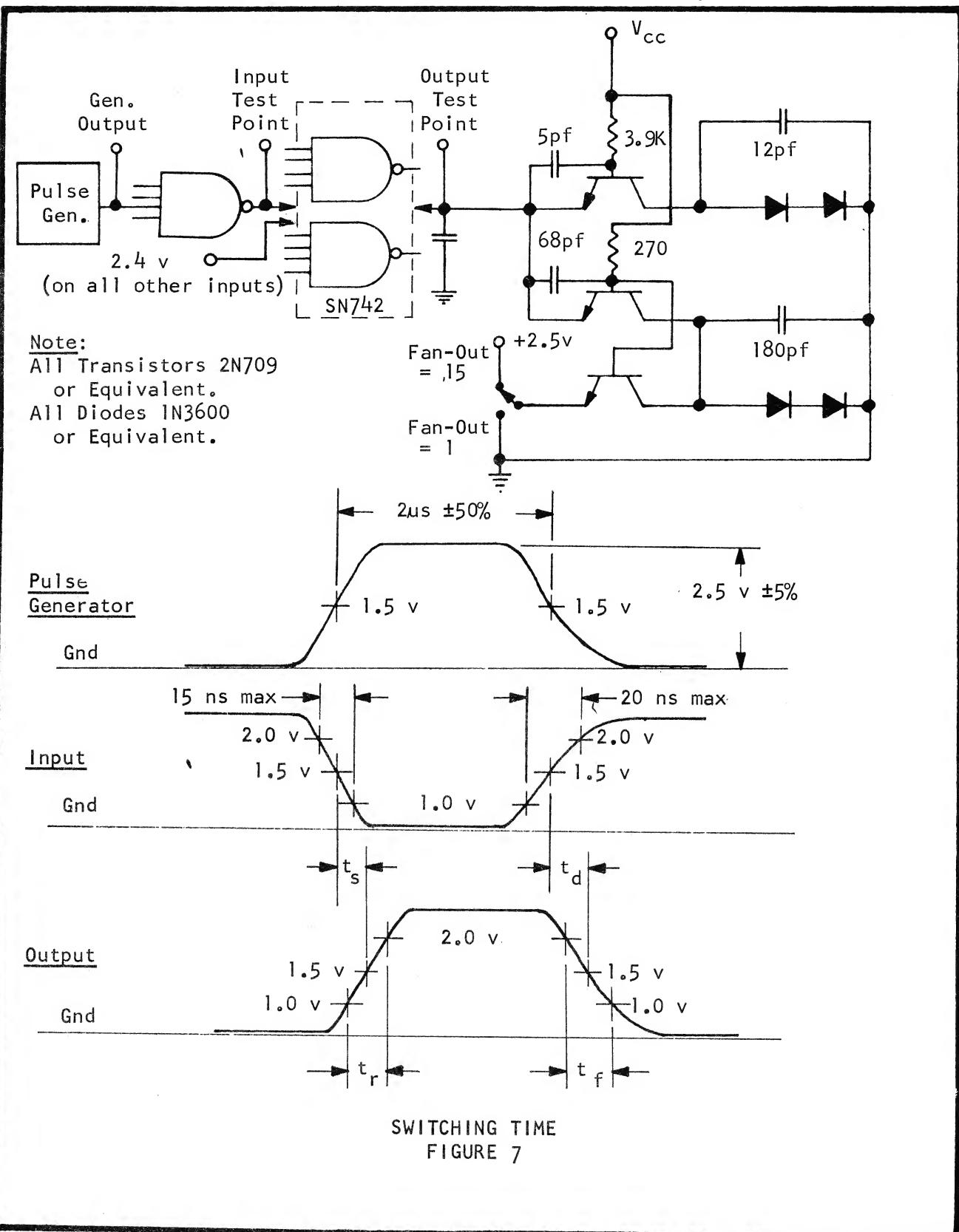
Short Current

Fig. 5



SWITCHING TIME
FIGURE 7

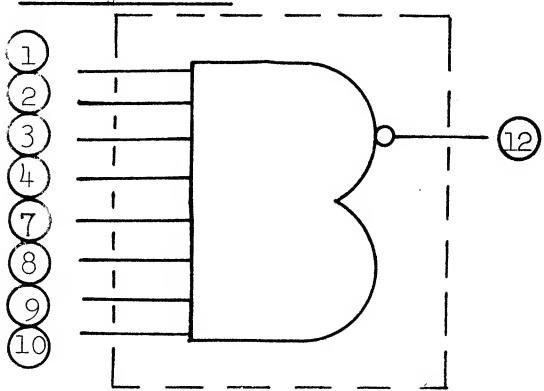
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DESCRIPTION

The SN743 is an 8-input, TTL, positive NAND gate capable of driving large fan-out and high capacity loads over the full military temperature range of -55°C to $+125^{\circ}\text{C}$. The SN743 is fabricated using diffused planar double epitaxial techniques.

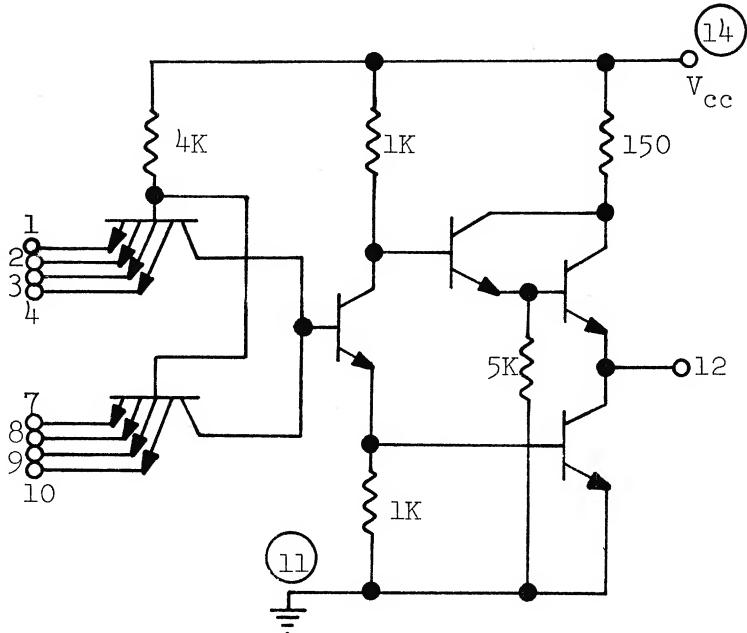
LOGIC DIAGRAMLOGIC

Positive NAND:

$$12 = \overline{(1)(2)(3)(4)(7)(8)(9)(10)}$$

Negative NOR:

$$12 = \overline{1+2+3+4+7+8+9+10}$$

CIRCUIT DIAGRAMTYPICAL ELECTRICAL CHARACTERISTICS

Fan-out	15
Propagation	25 ns
Noise Margin	600 mv
Power Dissipation	15 mw

August 1964

NETWORK CHARACTERISTICS

Absolute Maximum Ratings:

Supply Voltage	8 volts
Input Voltage	6 volts
Operating Ambient Temperature Range	-55°C to +125°C
Storage Temperature	-65°C to +150°C

Network Electrical Characteristics

All data applies for the following conditions unless otherwise noted:

Temperature: -55°C to +125°C

Fan-Out: 1 to 15

 $V_{cc} = 4.5$ volts

NETWORK PARAMETERS										MIN	MAX	UNIT	
Operating Supply Voltage										4.5	5.5	v	
Fan-Out										1	15		
Output ON Level (See Fig.1)	PIN	1	2	3	4	7	8	9	10				
$V_{cc} = 4.5$ v	+125°C	12	-	-	-	-	-	-	-	0.5		v	
$I_{12} = 20$ ma	-55°C	12	2.0	2.0	2.0	2.0	2.0	2.0	2.0	0.5		v	
Output OFF Level	(PIN	1	2	3	4	7	8	9	10			
$V_{cc} = 4.5$ v	(12	0.8	-	-	-	-	-	-	2.4		v	
$I_{12} = -2$ ma	(12	-	0.8	-	-	-	-	-	2.4		v	
(See Figure 2)	(12	-	-	0.8	-	-	-	-	2.4		v	
	(12	-	-	-	0.8	-	-	-	2.4		v	
	(12	-	-	-	-	0.8	-	-	2.4		v	
	(12	-	-	-	-	-	0.8	-	2.4		v	
	(12	-	-	-	-	-	-	0.8	2.4		v	
	(12	0.8	-	-	-	-	-	-	2.4		v	
Noise Immunity (Output ON Level)										300		mv	
(Output OFF Level)										400		mv	
Input Current (See Figure 4)	$V_{cc} = 5.5$ v	PIN	1	2	3	4	7	8	9	10			
		4	4.5	4.5	4.5	0	4.5	4.5	4.5	4.5	-1.6		ma
Short Current (See Fig.5)	$V_{cc}=5.5$ v; Pin 12 = 0 v	PIN	1	2	3	4	7	8	9	10			
		12	0	-	-	-	-	-	-	-	-20	-45	ma



PRELIMINARY SPECIFICATIONS

SOLID CIRCUIT
TYPE SN742
DUAL NAND GATE

R

NETWORK PARAMETERS										MIN	MAX	UNIT	
Input Leakage Current		PIN	1	12	13	14	6	7	8	9			
$V_{cc} = 5.5$ volts (See Figure 3)		1	4.5	0	0	0	-	-	-	-	150	ua	
		12	0	4.5	0	0	-	-	-	-	150	ua	
		13	0	0	4.5	0	-	-	-	-	150	ua	
		14	0	0	0	4.5	-	-	-	-	150	ua	
		6	-	-	-	-	4.5	0	0	0	150	ua	
		7	-	-	-	-	0	4.5	0	0	150	ua	
		8	-	-	-	-	0	0	4.5	0	150	ua	
		9	-	-	-	-	0	0	0	4.5	150	ua	
		1	5.5	0	0	0	-	-	-	-	1.0	ma	
		12	0	5.5	0	0	-	-	-	-	1.0	ma	
		13	0	0	5.5	0	-	-	-	-	1.0	ma	
		14	0	0	0	5.5	-	-	-	-	1.0	ma	
		6	-	-	-	-	5.5	-	-	-	1.0	ma	
		7	-	-	-	-	0	5.5	0	0	1.0	ma	
		8	-	-	-	-	0	0	5.5	0	1.0	ma	
		9	-	-	-	-	0	0	0	5.5	1.0	ma	
Short Current (See Fig. 5) $V_{cc} = 5.5$ volts Pins 2 and 10 = 0 volts		PIN	1	12	13	14	6	7	8	9			
		2	0	-	-	-	-	-	-	-	-20	-45	ma
		10	-	-	-	-	0	-	-	-	-20	-45	ma
Power Drain (From V_{cc}) $V_{cc} = 5.5$ volts		PIN	1	12	13	14	6	7	8	9			
		4	0	-	-	-	0	-	-	-		6	ma
		4	-	-	-	-	-	-	-	-		12	ma
Current (I_4) of Breakdown Voltage ($V_{cc} = 8$ volts) Pins 1 and 6 = 0 volts Temperature 25°C											12	ma	

SWITCHING TIME				MIN	MAX	UNIT
Delay Time (t_d) (See Figure 7) Fan-Out = 15				$C = 100$ pf		
				$C = 500$ pf		
Rise Time (t_r) (See Figure 7) Fan-Out = 1 and 15				$C = 100$ pf		
				$C = 500$ pf		
Fall Time (t_f) (See Figure 7) Fan-Out = 15				$C = 100$ pf		
				$C = 500$ pf		
Storage Time (t_s) (See Figure 7) Fan-Out				$C = 100$ pf		
				$C = 500$ pf		



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